Computational Imaging Prediction of Starburst-Effect Diffraction Spikes

Supplementary Information

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Supplementary Information A: Optical Theory

A.1 Path-Length Error Calculation

The geometry considered for the calculation of the aberrational phase shift kW(x, y) is illustrated in Figure A.1.



Figure A.1: An extension to the right half of Figure 1. F: in-focus image plane. W(x, y) is the optical pathlength accumulated between the reference spheres S_F and S_R (centered at the origins of F and R respectively) by the ideal ray l' when traced backward from the ideal image point on R to the point (x, y) within the exit pupil E'.

A.2 Aperture Edge-Spike Ratio

For even-sided apertures, the number of observable diffraction spikes will typically be identical to the number of aperture edges; for odd-sided apertures, the number of diffraction spikes will be *twice* the aperture edge count. This can be qualitatively understood by considering that the aperture edges are the most significant contributors to diffractive effects. At each edge, diffraction spikes emanate in both normal directions—on an even-sided aperture, there is an overlap of diffraction spikes emanating from opposite edges, but such overlaps do not occur on odd-sided apertures, therefore leading to the differing spike-edge ratios.

A.3 Gamma Correction (sRGB)

The processing pipeline applied to experimental and theoretical results entailed a gamma compression on the linear sRGB images in accordance with the sRGB standard, given by

$$C_{\rm srgb} = \begin{cases} 12.92C_{\rm linear} &, C_{\rm linear} \le a \\ 1.055C_{\rm linear}^{1/2.4} - 0.055 &, C_{\rm linear} > a, \end{cases}$$
(A.1)

where a = 0.0031308, and C is R, G, or B.

Supplementary Information B: Imaging System Characterization

B.1 Lens System Data

Table B.1 presents the pupil and principal plane positions of the examined AF Nikkor 50mm f/1.8D prime lens as extracted from existing literature [1].

E (mm)	E' (mm)	P (mm)	P'(mm)
48.8 ± 0.1	54.5 ± 0.1	48.5 ± 0.1	51.5 ± 0.1

Table B.1: Distances measured from sensor plane. E, E', P and P' denote the entrance pupil, exit pupil, front principal plane, and rear principal plane respectively.

B.2 Focusing Offset Calculations

For an object located at a distance $r_{\rm o}$ from the imaging sensor plane and a focusing distance of $r_{\rm f}$, it can be deduced from Equation (6) that

$$\delta z = -\frac{1}{2} \left(2f + \gamma + \sqrt{4f\gamma + \gamma^2} \right), \tag{B.1}$$

$$\Delta z = \frac{(r_{\rm f} - r_{\rm o}) \left(\sqrt{4f\gamma + \gamma^2 + 2f + \gamma}\right)}{-\sqrt{4f\gamma + \gamma^2 + 2f + r_{\rm f} - 2r_{\rm o} + z_{\rm p}}},\tag{B.2}$$

where $\gamma = z_p - r_f$, and Δz is as defined in Figure A.1. The latter can then be used in Equation (3) for the calculation of path-length error.

B.3 Sensor Response Function

In an ideal linear sensor, the recorded pixel value ζ is proportional to the charge liberated at the sensor element, until saturation where $\zeta = 1$.

$$\zeta \propto \int_0^\infty \chi(\lambda) N_\nu(\lambda) \,\mathrm{d}\lambda = \int_0^\infty \chi(\lambda) \left(\frac{\mathcal{M}(\lambda)A\lambda}{\mathfrak{h}c}t\right) \mathrm{d}\lambda,\tag{B.3}$$

where $N_{\nu}(\lambda)$ is the number of photons absorbed per unit wavelength, $\mathcal{M}(\lambda)$ is the incident spectral power distribution (SPD), A is the pixel area, t is the exposure time, \mathfrak{h} is Planck's constant, c is the speed of light, and $\chi(\lambda)$ is the quantum efficiency (QE) of the sensor. Keeping A and the light source identical, a linear response to exposure time can thus be expected for each colour channel, albeit with different gradients. In modern charge-coupled device (CCD) and complementary metal–oxide–semiconductor (CMOS) image sensors, this initially linear response is typically followed by a sharp plateau at the saturation point [2–5].

For monochromatic incident light of wavelength λ_0 and intensity I_0 , Equation (B.3) reduces to

$$\zeta \propto \frac{A\chi(\lambda_0)\lambda_0}{\mathfrak{h}c} \left(\frac{I_0 t}{\phi_0(\lambda_0)}\right),\tag{B.4}$$

where $\phi_0(\lambda_0)$ is the wavelength-specific reference radiant exposure, defined as the minimum exposure necessary to achieve sensor saturation. As the coefficients are solely dependent on sensor properties, they can be encompassed in the sensor response function \mathcal{Z} as introduced in Equation (5), yielding Equation (7) as presented.

It is thus apparent that unlike a complete polychromatic approach, the trichromatic approach adopted does not require knowlege of the complete SPD of the source and the QE of the imaging sensor. Instead, only empirical determination of \mathcal{Z} and ϕ_0 for each colour channel is required.



Figure B.1: Edge-detection of the exit pupil for an f/5.6 aperture. In the right image, in red: the edge-detected aperture shape.

B.4 Pupil Edge-Detection

A computational edge-detection method was used to characterize the size and geometry of the entrance and exit pupils. Figure B.1 presents the edge-detected pupil profile for the examined lens system.

References

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